M etal-Insulator Transitions in D egenerate H ubbard M odels $\mbox{and A}_{x}\mbox{C}_{60}$

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Abstract

M ott-H ubbard m etal-insulator transitions in N -fold degenerate H ubbard m odels are studied within the G utzw iller approximation. For any rational lling with x (integer) electrons per site it is found that m etal-insulator transition occurs at a critical correlation energy $U_c(N;x) = U_c(N;2N - x) = (N;x)j(N;x)j$ where is the band energy per particle for the uncorrelated Ferm i-liquid state and (N;x) is a geom etric factor which increases linearly with x. We propose that the alkalimetal doped fullerides A_xC_{60} can be described by a 3-fold degenerate H ubbard model. U sing the current estimate of band width and correlation energy this implies that most of A_xC_{60} , at integer x, are M ott-H ubbard insulators and A_3C_{60} is a strongly correlated metal. PACS numbers: 71.10.+x,71.30.+h,74.70 W

The discovery of superconductivity in A_3C_{60} [1] has spurred great interest in alkalim etal doped fullerides [2]. Beside A_3C_{60} , stable phases such as Rb_1C_{60} , Na_2C_{60} , K_4C_{60} were synthesized [2,3]. One unusual property is that except A_3C_{60} all integer x phases are found to behave like insulators [4]. This contradicts the band structure calculations which imply that all of them are metals due to the 3-fold degeneracy of the t_{1u} molecular orbitals which form ing the conduction bands [5]. In this letter we show that the strong (compared with the band width) intram olecular electron-electron correlation is responsible for this unusual property. The results we have obtained also shed light on the instability of the non-integer x phases [6].

The existence of strong correlation in pure C $_{60}$ is supported by spectroscopy experiments. Photoem ission shows an insulating gap of 2.6eV, while the photo-conductivity and absorption indicate excitation at 1.6eV. This discrepancy is interpreted as due to strong correlation which results in a large excitonic binding energy. The estimated correlation energy U 1eV [4,7,8] is much larger than the conduction band width W 0:2 0:4eV [5,10]. Thus, it has been suggested that that A $_3$ C $_{60}$ is a M ott-H ubbard insulator and the superconducting phase is non stoichiom etric [7]. However, structural, transport and spectroscopic measurements show that the superconducting phase is stoichiom etric and there is no evidence of insulating behavior in A₃C₆₀. Even more interesting is that for x € 3 integer stoichiom etric phases no m etallic behavior have been observed so far. Therefore neither a simple Hubbard model which prefers insulating at half $\lim (x = 3)$, nor the $\sin p$ le band $\lim g = 0$ which predict m etallic behavior for all phases, can explain the unusual m etal-insulator transitions observed.

C learly the 3-fold degeneracy of the conduction band can not be neglected. This leads us to study the general N-fold degenerate H ubbard m odel at rational llings. We not that the unusual metal-insulator transitions observed can be understood in term of Mott-H ubbard transition in the degenerate H ubbard model. It is found that for a general N-fold degenerate H ubbard model at rational lling x=2N, where the average number of electrons per site (x) is an integer, the metal-insulator transition occurs at a critical $U_{\rm c}$ which increases with both

x and N . U_c is found to be the largest at half—lling x=N for a given degeneracy N (except N=2). Therefore it is possible that the system—is a metal at half—lling while insulating away from—it. Our results lay a solid theoretical foundation for the interpretation that $A_x C_{60}$ are either M ott-Hubbard insulators or strongly correlated metals and provide a rationale to understand the unusual metal-insulator transitions in this family of materials and molecular metals in general.

Consider the general N -fold degenerate Hubbard model with the correlation energy U independent of orbitals and spins

$$H = \sum_{i \neq j; j}^{X} t_{i \neq j}^{\dagger} c_{j}^{\dagger} c_{i;} + \frac{U}{2} \sum_{i \neq j}^{X} n_{i;} n_{i;}; \qquad (1)$$

where = (r;) include both spin () and orbital (r) indices; $n_{i;} = c_{i;}^{\dagger} c_{i;}$ are number operators. Let L be the size of the lattice and M be the total number of electrons. By rational lling we mean that the average number of electrons per site x = M = L is an integer. For such a lling there exists a well de ned insulating state where there are exactly x electrons localized at each site. O byiously for a su ciently large U hopping is forbidden, and the the ground state is insulating. As U decreases a metal-insulator transition, at a certain critical U_c , is expected. For the case of the non-degenerate Hubbard model the only rational lling is the half lling (N = x = 1); in this case it is well known that the ground state at large U is an ordered magnetic insulator [9]. For the degenerate Hubbard model, in general, the insulating state could also be ordered. However, we will consider the param agnetic (or disordered) insulating state only because our primary interest is $A_x C_{60}$, where the lattice is non bi-partile and large amount of intrinsic disorders are known to exist [10,11].

In the insulating state, the kinetic energy is zero and the total energy per site E_0 is given by the correlation energy $PE = \frac{U}{2}x(x-1)$. Imagining a situation very close to the metalinsulation transition such that only one site has x+1 electrons, the correlation costs U while the kinetic energy gained for the excitation is of the order W. Since there are x electrons per site, there are x possible ways of making such an excitation. Therefore one might expect

 $U_{c}(x)$ xW [12].

In the case of the non-degenerate H ubbard m odel at half lling the rigorous result $U_c = 8j j = 2W$ was obtained by B rinkm an and R ice [13] within the G utzw iller approximation [14]. The central point of G utzw iller approximation is to associate a projection factor with every doubly occupied site, assuming that the many-body wavefunction can be written as a superposition of states with dierent numbers of doubly occupied sites. The optimal is determined variationally by calculating the expectation value of the H amiltonian. In the thermodynamic limit the summation over is dominated by the optimal term, then the kinetic and potential energies can be calculated by counting the number of congurations which contribute.

We have carried out sim ilar calculations rigorously for the general N-fold degenerate H ubbard model in a lim it close to the metal-insulator transition. The details of counting are rather tedious and will be published elsewhere [15]. Here we will simply state assumptions and results and discuss their implications for A_xC_{60} .

Let x be the average number of electrons per site and L be the total number of sites. We assume that there is complete permutation symmetry between all orbitals and spins, so the number of electrons occupying each = (r;) state is $m = \frac{xL}{2N}$. Near the metalinsulator transition the probability that a site is occupied by more than x+1 electrons is very small as it costs 2U or more energy. Thus we assume that each site can only be $\mbox{lem pty}$ " (x = 1 electrons), $\mbox{lingly-occupied}$ " (x electrons) or $\mbox{loubly-occupied}$ " (x + 1 electrons). Let 2N = L be the total number of doubly occupied sites, then by symmetry the number of empty sites is also 2N = Every doubly occupied site costs a correlation energy U with respect to the insulator state where there are exactly x electrons on every site. The Gutzwiller wavefunction is constructed from the uncorrelated Slater determinant $\mbox{local} L > = \mbox{local} L = \mbox{local} L$

This wave function is a linear combination of a large number of states with dierent. Following the original calculation of Gutzwiller, the expectation value of the Hamiltonian is dominated by the state with the optimal which is to be determined variationally. After a lengthy derivation the average energy per particle with respect to the paramagnetic insulating state is found to be [15]

$$E (N;x) = Q (N;x; ;m) (x) + \frac{1}{m}U;$$
 (3)

where (x) is the kinetic (band) energy per particle in the uncorrelated state with the center of the band chosen to be zero, (x = 2N) = 0. The quotient Q, which rejects the reduction of the hopping term in the correlated state [14,15], is given by

$$Q(N;x) = \frac{N;x}{m^{2}} (m - 2x) + \frac{(m - 2x)^{2}}{N;x};$$
(4)

w here

and the projection parameter is

$$= \begin{cases} \frac{8}{x} \frac{2x}{m \cdot 2x} & \text{if } x = 1 \text{ or } 2N & 1 \\ \frac{x}{m \cdot 2x} & \text{if } 2 & x \cdot 2N & 2 \end{cases}$$

$$(6)$$

Substituting eqs.4-6 into Eq. (3) and m in im izing the energy with respect to = =m leads to

$$=\frac{1}{4x}\left(1-\frac{U}{U_{c}}\right) \tag{7}$$

and the energy per particle

$$E_0 = \frac{(N;x)}{8x} (1 \frac{U}{U_c})^2;$$
 (8)

where U is given by

$$U_{c}(N;x) = (N;x)j(N;x)j = \begin{cases} 8 & \frac{2N \times x}{2N-1} & 1 + \frac{q \frac{2N-1}{2N-1}}{N} & 2 & 1 \\ \frac{2N \times x}{2N-1} & 1 + \frac{q \frac{2N-1}{2N-1}}{N} & 2 & 1 \end{cases}$$

$$(9)$$

$$4xj(N;x)j \qquad \text{if } 2 \times 2N = 2 :$$

As U increases toward U_c , the number of doubly occupied states approach zero. Thus the M ott-H ubbard transition occurs at U_c .

Eq.9 is the main result of this paper. Several points are worth mentioning. a) The particle-hole symmetry is preserved if j (N;x) j = $\frac{x}{2N-x}$ j (N;2N x) j this is expected because the starting H am iltonian Eq. (1) contains particle-hole symmetry. b) For N = 1 the only rational lling is half lling x=1, the B rinkman-R ice result $U_c = 8j$ j is recovered. c) Regardless of the band structure, U_c generally increases with x reaching the maximum at half lling x = N (N = 2 is an exception); thus, for a degenerate H ubbard system it is more discult for it to become a M ott insulator. d) The above results apply only to integer x. For non-integer x, if U is larger than U_c , there will be tendency for the system to phase separate into integer phases to lower the total energy. This may explain the experimental observation that non-integer x phases I are not stable $A_x C_{60}$ where the alkali ions can segregate together with electrons which screen out the long range C oulom b repulsion. Details of this issue will be explored elsewhere.

To make a quantitative estimate, one needs to know the band structure. In the case of a at band with the bandwidth W , $(N;x) = \frac{x-2N}{4N}W$. One obtains the simple result $U_c(N;x) = \frac{x(2N-x)}{N}W$ (x & 1;2N 1). This agrees qualitatively with the simple argument discussed earlier. Fig.1 shows plots of $U_c=W$ vs x=2N for several N values.

Now let us turn to the speci c application of the above results to the metal-insulator transitions in A_xC_{60} . It is known that each alkalimetal donates one electron and that the conduction band is formed by overlap of the 3-fold degenerate t_{lu} molecular orbitals. For x=1;3;4 structures are known to be rhombohedral, face-center-cubic and body-center-tetragonal, respectively [3]. For all these structures LDA ab initio calculations suggest that all of them are metals [5]. Experimentally, except x=3, all phases with integer x are found to be insulating. It has also been shown that the band structure can be accurately represented by a 3-band tight-binding model, in particular the density of states was shown to be approximately at due to the intrinsic orientational disorder [10]. The band width W determined from both experiments [16] and calculations [5,10] is very small, W 0.2 0.4eV.

On the other hand, spectroscopic studies [4,7] and theoretical calculations [8] suggest that the intram olecular electron correlation energy is around U 1eV. The value of U is expected to remain unchanged with doping because the screening is provided by the large number of molecular orbitals above t_{1u} , which is not a ected by the doping. From Eq. (9) and assuming a at band one obtains $U_c(x;N=3)=W=2:6;2:67;3$ respectively for x=1;2;3. Thus if the parameters are such that 2:67W<U<3W, which is where the current best estimate of W and U fall, then the whole family of A_xC_{60} for x=1;2;4;5 are M ott-H ubbard insulators while x=3 could be a strongly correlated metal. Of course we caution that the U_c calculated here only represents the lower bound; however, we expect the qualitative results $U_c(N;x)=U_c(N;x)$ and $U_c(N;x)=U_c(N;x)$ and $U_c(N;x)=U_c(N;x)$ by W will hold for the exact $U_c(N;x)=U_c(N;x)$

In conclusion we have studied M ott-H ubbard transitions in the N -fold degenerate H ubbard m odel within the G utzw iller approximation. It is shown that for any integer number of electrons per site there exists a critical correlation energy U_c above which the system is a M ott-H ubbard insulator. U_c is found to be sensitive to both the degeneracy and lling. We propose that the family of materials A_xC_{60} can be described by a 3-fold degenerate H ubbard model. With reasonable estimates for the band width and the intramolecular correlation energy, we show that it is possible that form ost integer phases (x = 1; 2; 4; 5) the materials are M ott-H ubbard insulators and A_3C_{60} is likely a strongly correlated metal despite the fact that U is several times of the band width.

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- [12] Notice that in the Hartreem ean eld approximation it is straightforward to show that the expectation of Hubbard U term is $x\frac{2N-1}{4N}U$ per particle, while the average kinetic energy is $(x) = \frac{x-2N}{4N}W$ for a at band with the band width W . Thus, the energy gain with respect to the disordered insulating state is $E = \frac{x-2N}{4N}W$ U). Thus $U_c = W$ independent of N and x.
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FIGURES

FIG. 1. Phase diagrams for M ott-Hubbard metal-insulator transitions in N-fold degenerate Hubbard models. Shown are results for N = 2;3;4;5. For U > $U_c(N;x)$ the system is a M ott-Hubbard insulator. Note that only the points, corresponding to integer (x) number of electrons per site, are meaningful.